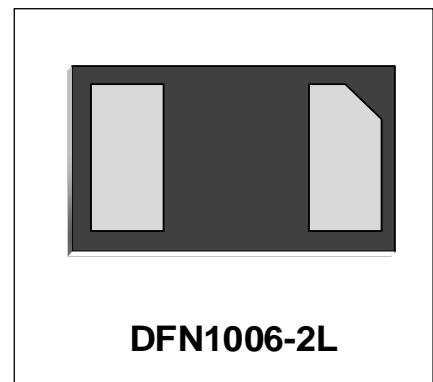




## Features

- Small Body Outline Dimensions:  
0.039" x 0.024" (1.0 mm x 0.60 mm)
- Protects one I/O or power line
- Low Clamping Voltage
- Ultra Low Capacitance: 0.5pF
- Working Voltage: 5 V
- Low Leakage Current
- Response Time is Typically < 1 ns



## IEC COMPATIBILITY (EN61000-4)

- IEC 61000-4-2 (ESD) ±20kV (air), ±20kV (contact)
- IEC 61000-4-4 (EFT) 40A (5/50ns)
- IEC 61000-4-5 (Lightning) 4A (8/20μs)

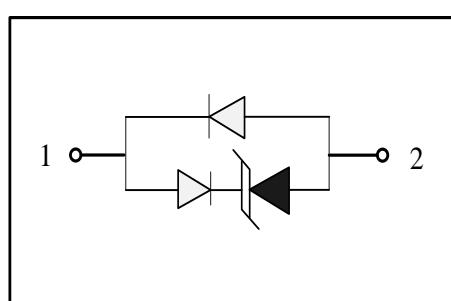
## Mechanical Characteristics

- DFN1006-2L package
- Molding compound flammability rating:  
UL 94V-0
- Marking: Marking Code
- Packaging: Tape and Reel per EIA 481
- RoHS Compliant

## Applications

- Laptop Computers
- Cellular Phones
- Digital Cameras
- Personal Digital Assistants (PDAs)

## Schematic & PIN Configuration

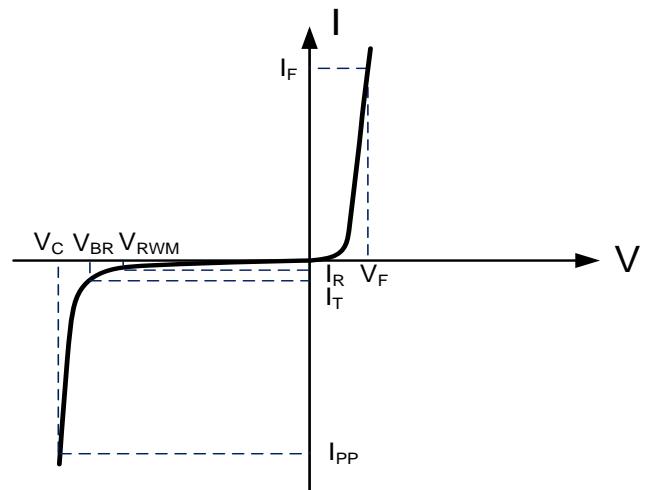


DFN-2L

<b>Absolute Maximum Rating</b>			
Rating	Symbol	Value	Units
Peak Pulse Power ( $t_p = 8/20\mu s$ )	$P_{PP}$	60	Watts
Peak Pulse Current ( $t_p = 8/20\mu s$ )	$I_{PP}$	4	A
Operating Temperature	$T_J$	-55 to +125	°C
Storage Temperature	$T_{STG}$	-55 to +150	°C

## Electrical Parameters ( $T=25^\circ C$ )

Symbol	Parameter
$I_{PP}$	Reverse Peak Pulse Current
$V_C$	Clamping Voltage @ $I_{PP}$
$V_{RWM}$	Reverse Stand-Off Voltage
$I_R$	Reverse Leakage Current @ $V_{RWM}$
$V_{BR}$	Breakdown Voltage @ $I_T$
$I_T$	Test Current
$I_F$	Forward Current
$V_F$	Forward Voltage @ $I_F$



## Electrical Characteristics

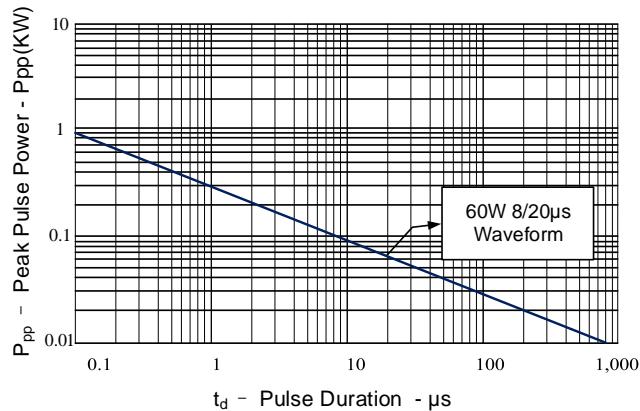
ES05DUCF-02						
Parameter	Symbol	Conditions	Minimum	Typical	Maximum	Units
Reverse Stand-Off Voltage	$V_{RWM}$				5	V
Reverse Breakdown Voltage	$V_{BR}$	$I_T=1mA$	6		10	V
Reverse Leakage Current	$I_R$	$V_{RWM}=5V, T=25^\circ C$			100	nA
Clamping Voltage	$V_C$	$I_{PP}=4.0A, t_p=8/20\mu s$		9	15	V
Dynamic Resistance <sup>1,2</sup>	$R_{DYN}$	$TLP=0.2/100ns$		0.56		Ω
ESD Clamping Voltage	$V_C$	$I_{PP} = 4A, t_p = 0.2/100ns (TLP)$		10.3		V
ESD Clamping Voltage	$V_C$	$I_{PP} = 16A, t_p = 0.2/100ns (TLP)$		17		V
Junction Capacitance	$C_j$	$V_R = 0V, f = 1MHz$		0.5	0.7	pF

### Notes

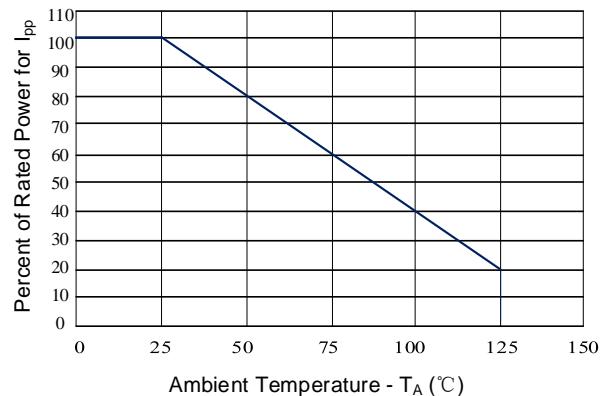
- 1、TLP Setting :  $t_p=100ns$ ,  $t_r=0.2ns$ ,  $I_{TLP}$  and  $V_{TLP}$  sample window: $t_1=70ns$  to  $t_2=90ns$ .
- 2、Dynamic resistance calculated from  $I_{PP}=4A$  to  $I_{PP}=16A$  using “Best Fit”.

## Typical Characteristics

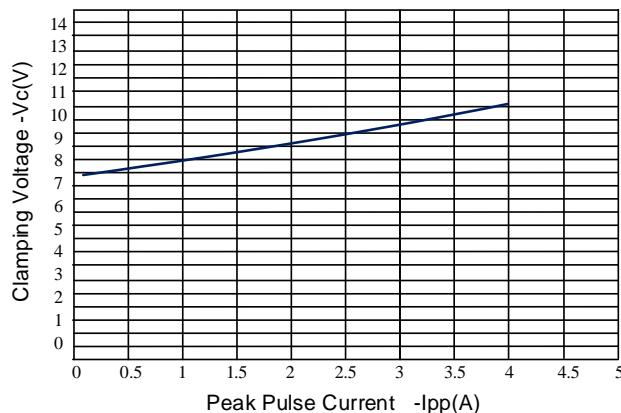
**Figure 1: Peak Pulse Power Vs Pulse Time**



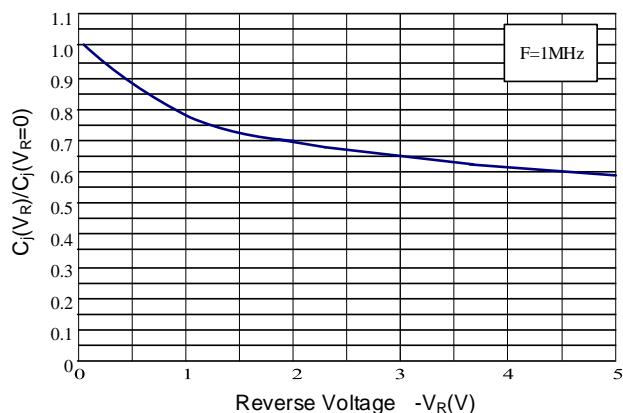
**Figure 2: Power Derating Curve**



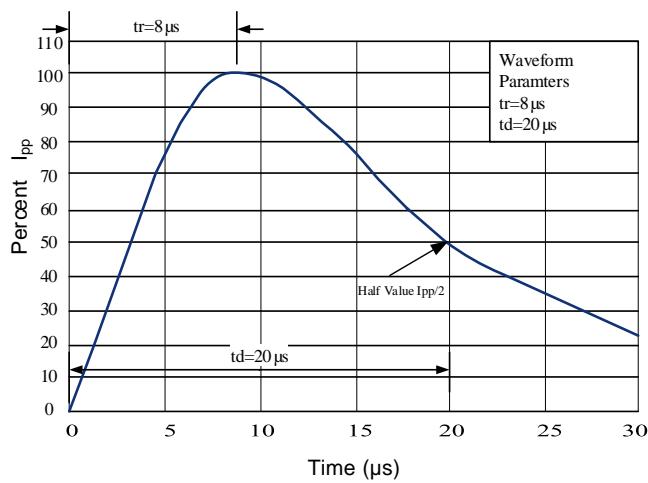
**Figure 3: Clamping Voltage vs. Peak Pulse Current**



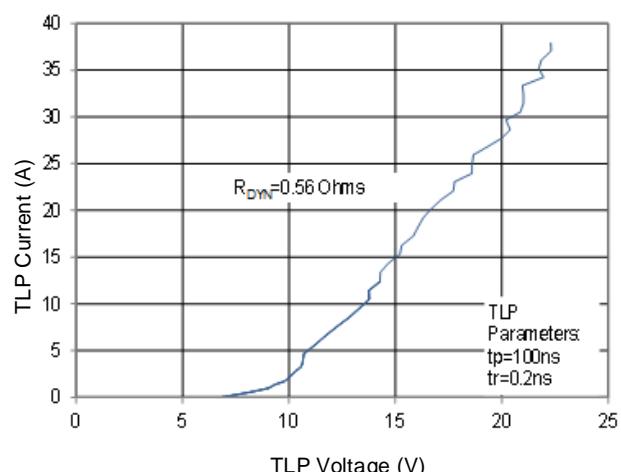
**Figure 4: Normalized Junction Capacitance vs. Reverse Voltage**



**Figure 5: Pulse Waveform**

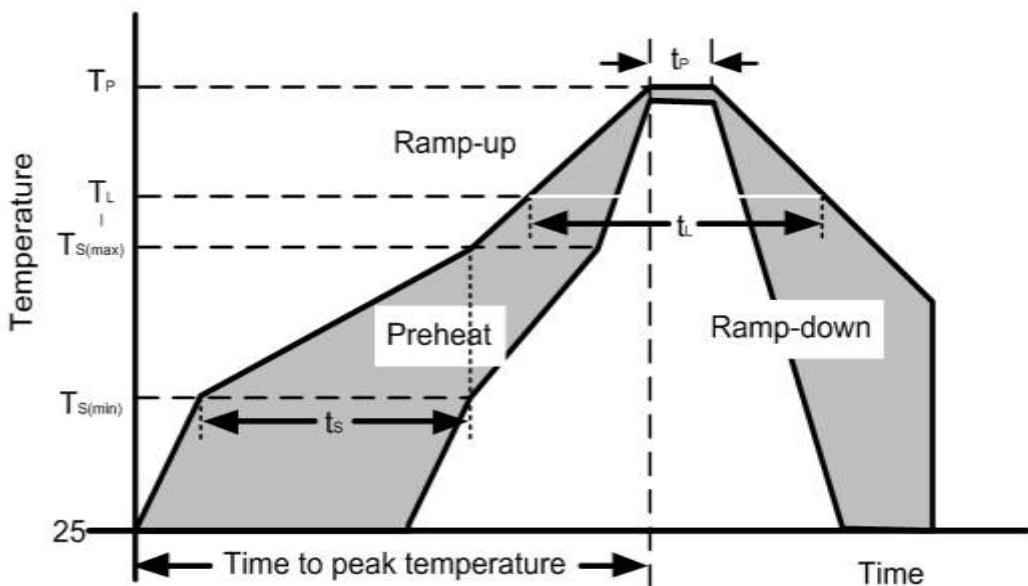


**Figure 6: TLP I-V Curve**

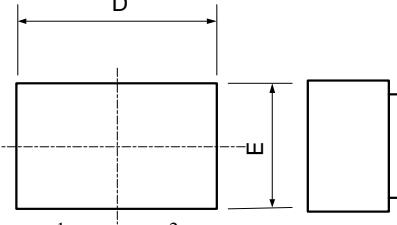
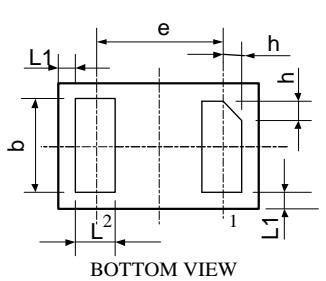


## Soldering Parameters

Reflow Condition		Pb – Free assembly
Pre Heat	Temperature Min ( $T_{s(min)}$ )	150°C
	Temperature Max ( $T_{s(max)}$ )	200°C
	Time (min to max) ( $t_s$ )	60 – 190 secs
Average ramp up rate (Liquidus Temp) ( $T_L$ ) to peak		5°C/second max
$T_{s(max)}$ to $T_L$ —Ramp-up Rate		5°C/second max
Reflow	Temperature ( $T_L$ ) (Liquidus)	217°C
	Temperature ( $t_L$ )	60 – 150 seconds
	Peak Temperature ( $T_P$ )	260+0/-5 °C
Time within actual peak Temperature ( $t_p$ )		20 – 40 seconds
Ramp-down Rate		5°C/second max
Time 25°C to peak Temperature ( $T_P$ )		8 minutes Max.
Do not exceed		280°C

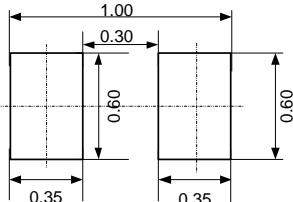


## Outline Drawing –DFN1006-2L

PACKAGE OUTLINE			
		BOTTOM VIEW	 DFN1006-2L
SYMBOL	MIN	NOM	MAX
A	0.45	0.50	0.55
A1	0	0.02	0.05
b	0.45	0.50	0.55
C	0.12	0.15	0.18
D	0.95	1.00	1.05
e	0.65BSC		
E	0.55	0.60	0.65
L	0.20	0.25	0.30
L1	0.05REF		
h	0.07	0.12	0.17

### Land Pattern



## Marking Codes

Part Number	Marking Code
ES05DUCF-02	1  2

## Package Information

Qty: 10k/Reel